Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	(cnt near fet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:56
L2	0	10/711083	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:55
L3	0	(cnt near fet) with stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:56
L4	141	(nanotube) with stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:57
L5	1697	(nanotube) with (mechanical or thermal or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:57
L6	1397	(carbon near nanotube) with (mechanical or thermal or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:57
L7	6	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) with (mechanical or thermal or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:58
L8	0	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) with (stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:58
L9	0	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) same (stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 18:59

L10	9	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) same (detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:01
EII	15	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) same (defective or sensor or sensed or sensing oor detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:01
L12	15	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) same (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:01
L13	14	(carbon near nanotube near5 (fet or (field adj effect adj transistor))) with (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:03
L14	1382	(cnt or cntfet or (cnt near fet) or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:04
L15	14	((carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:04
L16	1382	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:04
L17	1046	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) near10 (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:04

L18	18	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) near10 (defective or sensor or sensed or sensing or detect or detecting or detected or detection or detector or stress or strain).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:05
L19	0	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) near10 (stress or strain).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:05
L20	12	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) near10 (stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:05
L21	23	(cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (stress or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:05
L22	0	((cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (stress or strain)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:05
L23	23	((cnt or (carbon near nanotube near5 (fet or (field adj effect adj transistor)))) with (stress or strain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:07
L24	25	"6630772"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:07
L25	33	"6630772" or "6437329" or "20030218224" or "20010023986"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:11
L26	11	I25 and (stress or defect or strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:11
L27	11	I25 and (stress or defect or strain or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:11

L28	2	I25 and (stress or defect or strain or defective).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:12
L29	11	I25 and (stress or defect or strain or defective)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 19:12